INK0001AX SERIES

High speed switching Silicon N-channel MOSFET

Unit: mm

DESCRIPTION

INK0001AX is a Silicon N-channel MOSFET.

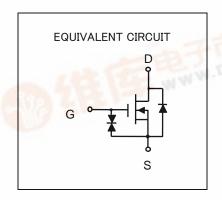
This product is most suitable for low voltage use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

- •Input impedance is high, and not necessary to consider a drive electric current.
- •Vth is low, and drive by low voltage is possible. Vth=0.6~1.2V
- •Low on Resistance. Ron=3.5 Ω (TYP)
- ·High speed switching.
- *Small package for easy mounting.

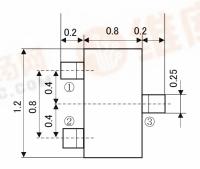
APPLICATION

high speed switching, Analog switching



OUTLINE DRAWING

INK0001AT2 (PRELIMINARY) INK0001AM1





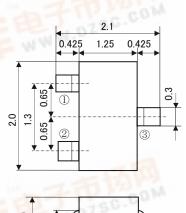
JEITA, JEDEC: — ISAHAYA: T-USM

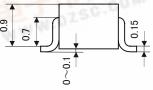
TERMINAL CONNECTOR

1:GATE

2: SOURCE

3: DRAIN





JEITA: SC-70 JEDEC: —

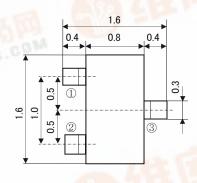
TERMINAL CONNECTOR

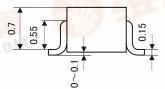
1: GATE

2:SOURCE

3:DRAIN

INK0001AU1





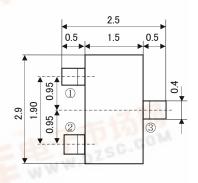
JEITA: SC-75A JEDEC: —

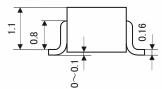
TERMINAL CONNECTOR

①:GATE ②:SOURCE

3:DRAIN

INK0001AC1





JEITA: SC-59 JEDEC: Similar to TO-236

T TERMINAL CONNECTOR

1:GATE

②:SOURCE

3: DRAIN



INK0001AX SERIES

High speed switching Silicon N-channel MOSFET

MAXIMUM RATING(Ta=25°C)

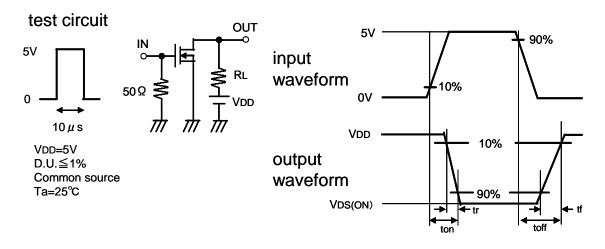
SYMBOL	PARAMETER	RATING				
	PARAMETER	INK0001AT2	INK0001AU1	INK0001AM1	INK0001AC1	UNIT
$V_{\scriptscriptstyle DSS}$	Drain-source voltage	50				
V_{GSS}	Gate-source voltage	±8				
I D	Drain current	100				
P _D	Total power dissipation (Ta=25°C)	125(※)	150	200		mW
Tch	Channel temperature	+125	+150			°C
Tstg	Range of Storage temperature	−55 ~ +125	−55 ~ +150			°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

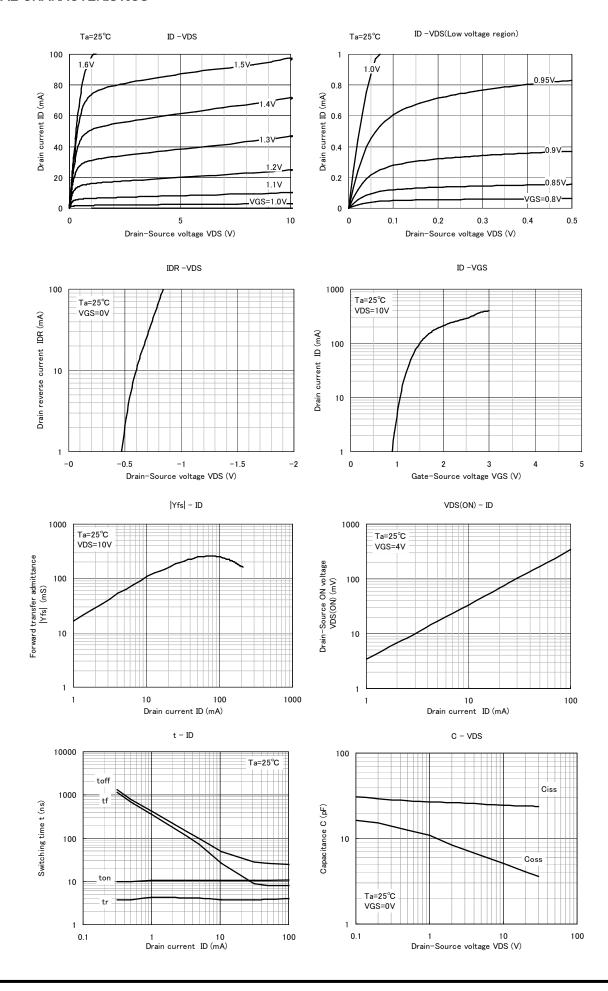
**package mounted on 9mm × 19mm × 1mm glass-epoxy substrate.

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D=100 \mu A, V_{GS}=0V$	50	_	-	V
I _{GSS}	Gate-source leak current	$V_{GS}=\pm5V, V_{DS}=0V$	_	_	±0.5	μΑ
I _{DSS}	Zero gate voltage drain current	V _{DS} =50V ,V _{GS} =0V	-	_	50	μΑ
V_{th}	Gate threshold voltage	I $_{\rm D}$ =250 μ A, V $_{\rm DS}$ = V $_{\rm GS}$	0.6	-	1.2	٧
Y _{fs}	Forward transfer admittance	V _{DS} =10V, I _D =0.1A	-	250	-	mS
R _{DS(ON)}	Static drain-source on-state resistance	I _D =100mA, V _{GS} =4.0V	_	3.5	-	Ω
Ciss	Input capacitance	V _{DS} =10V, V _{GS} =0V,f=1MHz	-	24	-	pF
Coss	Output capacitance	V _{DS} =10V, V _{GS} =0V,f=1MHz	-	5	-	pF
ton	Conit all in an Aire a	V _{DD} =5V , I _D =10mA	_	11	_	
toff	Switching time	V _{GS} =0∼5V	_	50	_	ns

Switching time test condition



TYPICAL CHARACTERISTICS





Marketing division, Marketing planning department

6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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